



### 30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

-2.6A

### **Features**

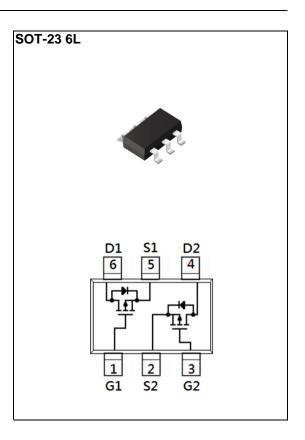
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@-10V, I<sub>D</sub>@-2.6A<115mΩ
- $R_{DS(ON)}$ ,  $V_{GS}@-4.5V$ ,  $I_{D}@-1.7A<150m\Omega$
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### **Mechanical Data**

• Case: SOT-23 6L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0005 ounces, 0.0142 grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	-30	V	
Gate-Source Voltage		V <sub>G</sub> s	<u>+</u> 20		
Continuous Drain Current(Note 4)		ID	-2.6	A	
Pulsed Drain Current <sup>(Note 1)</sup>		I <sub>DM</sub>	-10.4		
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	1.25	W	
	Derate above 25°C		10	mW/°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C	
Typical Thermal Resistance - Junction to Ambient <sup>(Note 3,4)</sup>		RөJA	100	°C/W	





## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250uA$	-1	-1.31	-2.1			
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-2.6A	-	93	115	mΩ		
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1.7A	-	116	150			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	-1	uA		
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA		
Dynamic <sup>(Note 5)</sup>								
Total Gate Charge	$Q_g$	V <sub>DS</sub> =-15V, I <sub>D</sub> =-2.6A, V <sub>GS</sub> =-10V <sup>(Note 1,2)</sup>	-	9.8	-	nC		
Gate-Source Charge	$Q_{gs}$		-	1.5	-			
Gate-Drain Charge	$Q_{gd}$		-	2.2	-			
Input Capacitance	Ciss	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHZ	-	396	-	pF		
Output Capacitance	Coss		-	47	-			
Reverse Transfer Capacitance	Crss		-	36	-			
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}\text{=-}15V, \ I_{D}\text{=-}2.6A,$ $V_{GS}\text{=-}10V,$ $R_{G}\text{=}6\Omega^{(Note\ 1,2)}$	-	5	-	ns		
Turn-On Rise Time	tr		-	30	-			
Turn-Off Delay Time	td <sub>(off)</sub>		-	25	-			
Turn-Off Fall Time	tf		-	8	-			
Drain-Source Diode								
Maximum Continuous Drain-Source			-	-	-1.5	А		
Diode Forward Current	Is							
Diode Forward Voltage	$V_{\text{SD}}$	Is=-1A, V <sub>GS</sub> =0V	-	-0.77	-1.2	V		

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

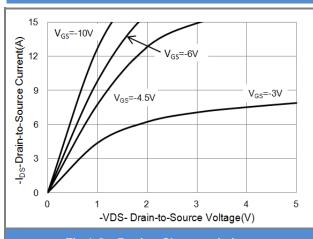
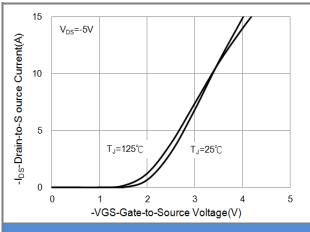


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

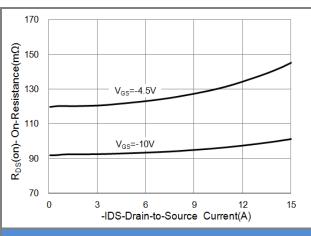


Fig.3 On-Resistance vs. Drain Current

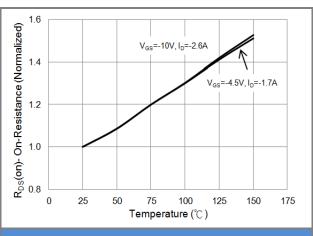
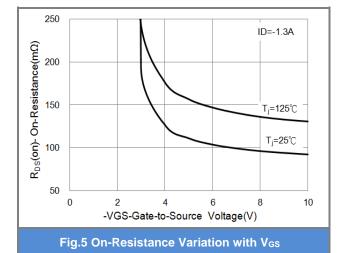


Fig.4 On-Resistance vs. Junction temperature



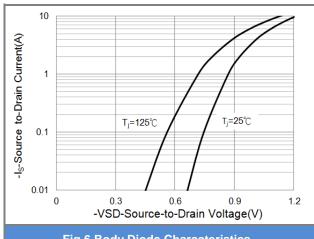


Fig.6 Body Diode Characteristics





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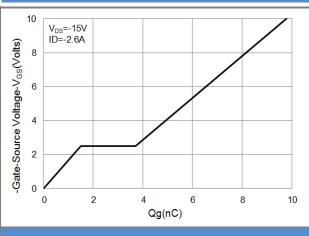


Fig.7 Gate-Charge Characteristics

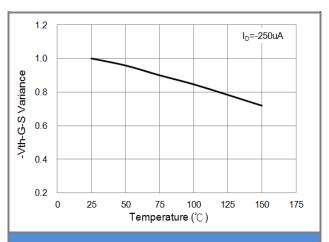


Fig.8 Threshold Voltage Variation with Temperature

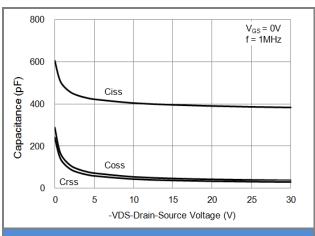


Fig.9 Capacitance vs. Drain-Source Voltage

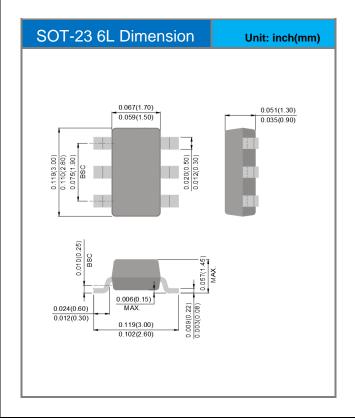


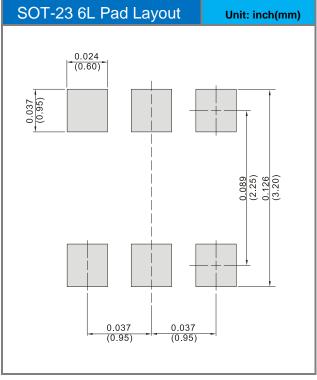


## Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJS6809-AU_S1_000A1	SOT-23 6L	3K pcs / 7" reel	ST9	Halogen free RoHS compliant

## **Packaging Information & Mounting Pad Layout**









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